

# SILICON TRANSISTOR 2SC3356

## MICROWAVE LOW NOISE AMPLIFIER NPN SILICON EPITAXIAL TRANSISTOR

#### **DESCRIPTION**

The 2SC3356 is an NPN silicon epitaxial transistor designed for low noise amplifier at VHF, UHF and CATV band.

It has dynamic range and good current characteristic.

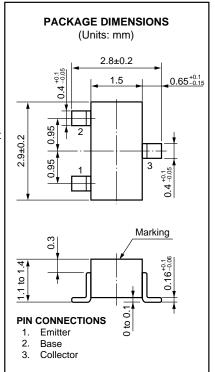
#### **FEATURES**

- · Low Noise and High Gain
  - NF = 1.1 dB TYP.,  $G_a = 11 dB TYP.$  @VcE = 10 V, Ic = 7 mA, f = 1.0 GHz
- · High Power Gain

MAG = 13 dB TYP. @VcE = 10 V, Ic = 20 mA, f = 1.0 GHz

#### ABSOLUTE MAXIMUM RATINGS (TA = 25 °C)

Collector to Base Voltage	Vсво	20	V
Collector to Emitter Voltage	Vceo	12	V
Emitter to Base Voltage	VEBO	3.0	V
Collector Current	Ic	100	mΑ
Total Power Dissipation	Рт	200	mW
Junction Temperature	$T_j$	150	°C
Storage Temperature	Tstg	-65 to +150	°C



#### ELECTRICAL CHARACTERISTICS (TA = 25 °C)

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
Collector Cutoff Current	Ісво			1.0	μА	Vcb = 10 V, IE = 0
Emitter Cutoff Current	ІЕВО			1.0	μА	VEB = 1.0 V, Ic = 0
DC Current Gain	hfe*	50	120	300		VcE = 10 V, Ic = 20 mA
Gain Bandwidth Product	f⊤		7		GHz	Vce = 10 V, Ic = 20 mA
Feed-Back Capacitance	Cre**		0.55	1.0	pF	VcB = 10 V, IE = 0, f = 1.0 MHz
Insertion Power Gain	S <sub>21</sub> e   <sup>2</sup>		11.5		dB	Vce = 10 V, Ic = 20 mA, f = 1.0 GHz
Noise Figure	NF		1.1	2.0	dB	Vce = 10 V, Ic = 7 mA, f = 1.0 GHz

Pulse Measurement PW  $\leq$  350  $\mu$ s, Duty Cycle  $\leq$  2 %

#### **h**FE Classification

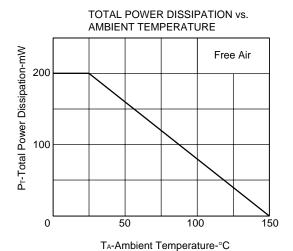
Class	R23/Q *	R24/R *	R25/S *
Marking	R23	R24	R25
hfe	50 to 100	80 to 160	125 to 250

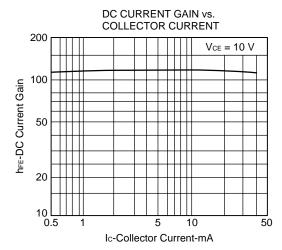
Old Specification / New Specification

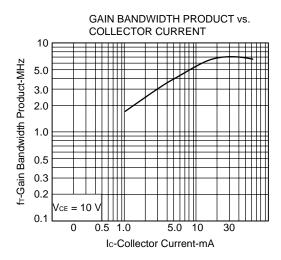
<sup>\*\*</sup> The emitter terminal and the case shall be connected to the guard terminal of the three-terminal capacitance bridge.

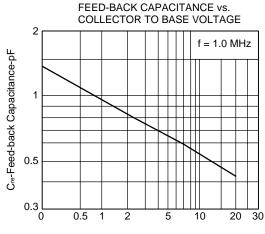


### TYPICAL CHARACTERISTICS (TA = 25 °C)

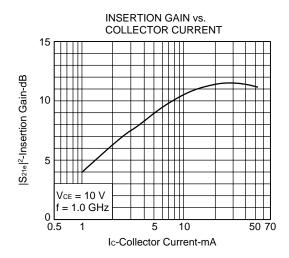


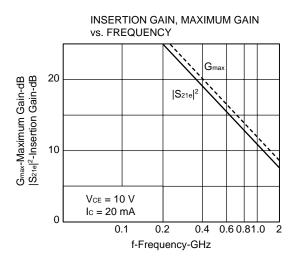




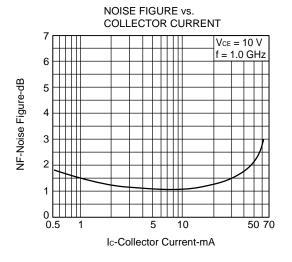


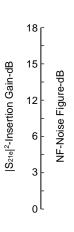


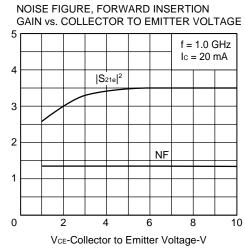












### **S-PARAMETER**

Vce = 10 V, Ic = 5 mA, Zo = 50  $\Omega$ 

f (MHz)	S <sub>11</sub>	∠ S <sub>11</sub>	S <sub>21</sub>	∠ <b>S</b> 21	S <sub>12</sub>	∠ <b>S</b> 12	S <sub>22</sub>	∠ <b>S</b> 22
200	0.651	-69.3	10.616	129.3	0.051	59.2	0.735	-28.1
400	0.467	-113.3	6.856	104.4	0.071	54.4	0.550	-34.1
600	0.391	-139.3	4.852	90.9	0.086	56.0	0.468	-33.9
800	0.360	-159.2	3.802	81.2	0.101	59.1	0.426	-33.6
1000	0.360	-176.9	3.098	72.9	0.118	61.0	0.397	-35.7
1200	0.361	172.7	2.646	67.3	0.137	63.5	0.373	-38.3
1400	0.381	160.3	2.298	59.3	0.157	63.3	0.360	-43.0
1600	0.398	152.2	2.071	55.2	0.180	64.1	0.337	-45.9
1800	0.423	143.3	1.836	49.0	0.203	63.7	0.320	-52.3
2000	0.445	137.6	1.689	46.2	0.220	64.7	0.302	-52.2

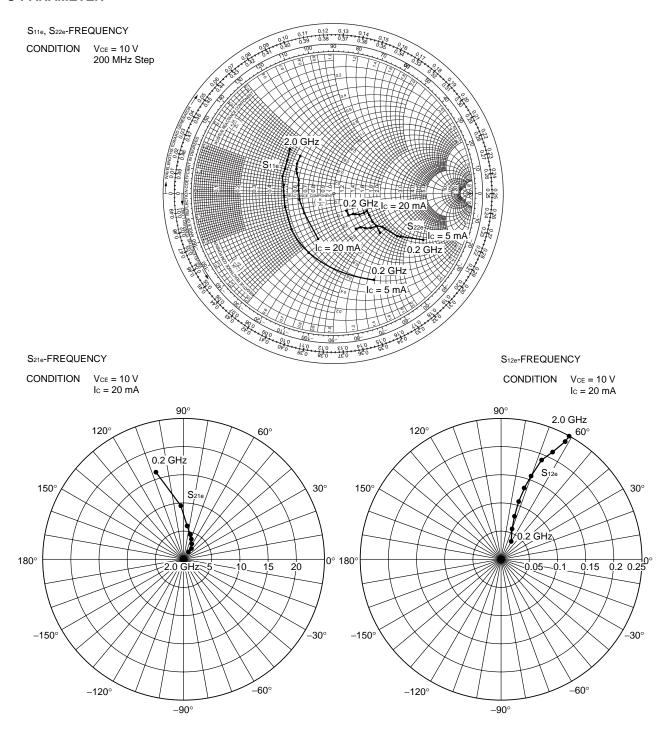
 $V_{\text{CE}}$  = 10 V, Ic = 5 mA, Zo = 50  $\Omega$ 

f (MHz)	S <sub>11</sub>	∠ <b>S</b> 11	S <sub>21</sub>	∠ <b>S</b> 21	S <sub>12</sub>	∠ <b>S</b> 12	S22	∠ <b>S</b> 22
200	0.339	-107.0	16.516	108.7	0.035	66.1	0.459	-36.6
400	0.258	-147.3	8.928	92.1	0.060	71.0	0.343	-32.9
600	0.243	-167.7	6.022	83.0	0.085	71.9	0.305	-29.9
800	0.242	177.0	4.633	76.2	0.109	72.2	0.284	-29.4
1000	0.260	164.5	3.744	69.9	0.136	70.4	0.266	-31.7
1200	0.269	157.6	3.193	65.7	0.160	69.9	0.246	-35.0
1400	0.294	148.7	2.750	58.8	0.187	66.7	0.233	-40.4
1600	0.314	143.1	2.479	55.5	0.212	65.2	0.208	-43.6
1800	0.343	136.5	2.185	50.1	0.238	62.4	0.190	-50.5
2000	0.367	131.4	2.016	47.8	0.254	61.6	0.173	-48.3

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#### **S-PARAMETER**



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Anti-radioactive design is not implemented in this product.

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